

GT75HH120T2H

IGBT Module

Preliminary Data

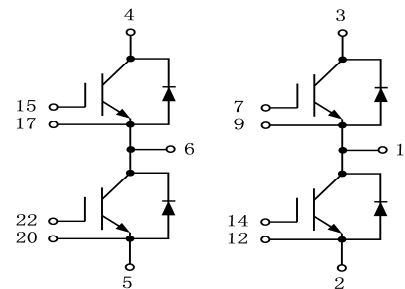
Features:

- Short Circuit Rated 10 μ s
- Low Saturation Voltage: $V_{CE(sat)} = 1.90V @ I_C = 75A, T_C = 25^\circ C$
- Low Switching Loss
- 100% RBSOA Tested (2 \times I_C)
- Low Stray Inductance
- Lead Free, Compliant with RoHS Requirement



Applications:

- Welding Machine、Cutting Machine
- Plating Power Supply、Induction Heating
- SMPS、UPS



IGBT, Inverter

Maximum Rated Values($T_C = 25^\circ C$ Unless otherwise specified)

V_{CES}	Collector-Emitter Blocking Voltage		1200	V
V_{GES}	Gate-Emitter Voltage		± 20	V
I_C	Continuous Collector Current	$T_C = 80^\circ C,$	75	A
		$T_C = 25^\circ C$	150	A
I_{CM}	Peak Collector Current Repetitive	$T_J = 175^\circ C$	150	A
t_{SC}	Short Circuit Withstand Time		>10	μ s
P_D	Maximum Power Dissipation (IGBT)	$T_C = 25^\circ C$ $T_{Jmax} = 175^\circ C$	520	W

Electrical Characteristics of IGBT ($T_C=25^\circ\text{C}$ Unless otherwise specified)

Static characteristics

Symbol	Description	Conditions	Min	Typ	Max	Unit
$V_{GE(th)}$	Gate-Emitter Threshold Voltage	$I_C = 1 \text{ mA}, V_{CE} = V_{GE}$	5.0	5.5	6.0	V
$V_{CE(sat)}$	Collector-Emitter Saturation Voltage	$I_C = 75\text{A}, V_{GE} = 15\text{V}$	$T_J = 25^\circ\text{C}$	1.90	2.10	V
			$T_J = 125^\circ\text{C}$	2.20		V
I_{CES}	Collector-Emitter Leakage Current	$V_{GE} = 0\text{V}, V_{CE} = V_{CES}, T_J = 25^\circ\text{C}$			1	mA
I_{GES}	Gate-Emitter Leakage Current	$V_{GE} = \pm 20\text{V}, V_{CE} = 0\text{V}, T_J = 25^\circ\text{C}$			200	nA
C_{ies}	Input Capacitance	$V_{CE} = 25\text{V}, V_{GE} = 0\text{V}, f = 1\text{MHz}$		10.4		nF
C_{oes}	Output capacitance			0.56		nF

Switching Characteristics

$t_{d(on)}$	Turn-on Delay Time	$V_{CC} = 600\text{V}, I_C = 75\text{A}, R_G = 15\Omega, V_{GE} = \pm 15\text{V},$ Inductive Load	$T_J = 25^\circ\text{C}$		190		ns
			$T_J = 125^\circ\text{C}$		170		
t_r	Rise Time		$T_J = 25^\circ\text{C}$		100		ns
			$T_J = 125^\circ\text{C}$		110		
$t_{d(off)}$	Turn-off Delay Time		$T_J = 25^\circ\text{C}$		270		ns
			$T_J = 125^\circ\text{C}$		280		
t_f	Fall Time		$T_J = 25^\circ\text{C}$		160		ns
			$T_J = 125^\circ\text{C}$		240		
E_{on}	Turn-on Switching Loss		$T_J = 25^\circ\text{C}$		5.77		mJ
			$T_J = 125^\circ\text{C}$		6.90		
E_{off}	Turn-off Switching Loss	$T_J = 25^\circ\text{C}$		3.54		mJ	
		$T_J = 125^\circ\text{C}$		5.60			
Q_g	Total Gate Charge	$T_J = 25^\circ\text{C}$		630		nC	
RBSOA	RBSOA	$I_C = 150\text{A}, V_{CC} = 1050\text{V}, V_p = 1200\text{V}, R_G = 15\Omega, V_{GE} = +15\text{V to } 0\text{V}, T_J = 150^\circ\text{C}$	Trapezoid				
SCSOA	SCSOA	$V_{CC} = 600\text{V}, V_{GE} = 15\text{V}, T_J = 150^\circ\text{C}$	10			μs	
$R_{\theta JC}$	Junction-To-Case (IGBT)			0.29		$^\circ\text{C/W}$	



Diode, Inverter

Maximum Rated Values ($T_C=25^{\circ}\text{C}$ Unless otherwise specified)

V_{RRM}	Repetitive peak reverse voltage	1200	V
I_F	Diode Continuous Forward Current	75	A
I_{FM}	Peak FWD Current Repetitive	150	A

Electrical Characteristics of FWD ($T_C=25^{\circ}\text{C}$ Unless otherwise specified)

V_{FM}	Forward Voltage	$I_F = 75\text{A}$, $V_{GE} = 0\text{V}$	$T_J = 25^{\circ}\text{C}$	2.00	V
			$T_J = 125^{\circ}\text{C}$	2.20	
I_{rr}	Peak Reverse Recovery Current	$I_F = 75\text{A}$, $di/dt = 700\text{A}/\mu\text{s}$, $V_{rr} = 600\text{V}$, $V_{GE} = -15\text{V}$	$T_J = 25^{\circ}\text{C}$	35	A
			$T_J = 125^{\circ}\text{C}$	40	
Q_{rr}	Reverse Recovery Charge	$I_F = 75\text{A}$, $di/dt = 700\text{A}/\mu\text{s}$, $V_{rr} = 600\text{V}$, $V_{GE} = -15\text{V}$	$T_J = 25^{\circ}\text{C}$	5.7	μC
			$T_J = 125^{\circ}\text{C}$	9.52	
E_{rec}	Reverse Recovery Energy	$I_F = 75\text{A}$, $di/dt = 700\text{A}/\mu\text{s}$, $V_{rr} = 600\text{V}$, $V_{GE} = -15\text{V}$	$T_J = 25^{\circ}\text{C}$	1.92	mJ
			$T_J = 125^{\circ}\text{C}$	3.80	
$R_{\theta JC}$	Junction-To-Case Diode		0.56		$^{\circ}\text{C}/\text{W}$

Module

Symbol	Description	Conditions	Min	Typ	Max	Unit
V_{iso}	Isolation Voltage(All Terminals Shorted)	$f = 50\text{Hz}$, 1minute	2500			V
T_J	Maximum Junction Temperature				175	$^{\circ}\text{C}$
T_{JOP}	Maximum Operating Junction Temperature Range		-40 +150			$^{\circ}\text{C}$
T_{stg}	Storage Temperature		-40 +125			$^{\circ}\text{C}$
$R_{\theta CS}$	Case-To-Sink (Conductive Grease Applied)			0.1		$^{\circ}\text{C}/\text{W}$
M	Power Terminals Screw:M5		3.0		5.0	N·m
M	Mounting Screw:M6		4.0		6.0	N·m
G	Weight			280		g

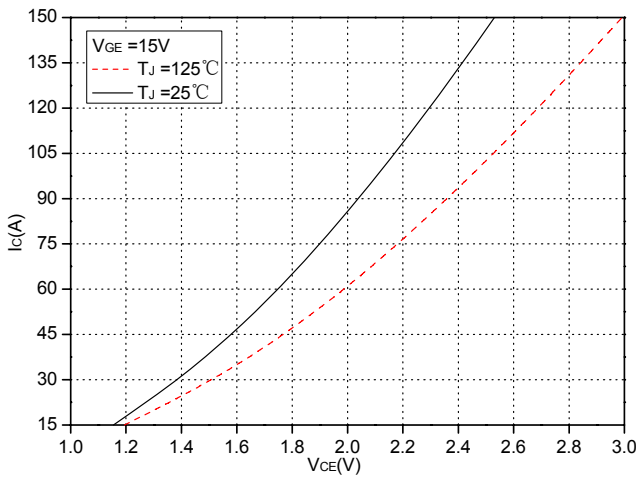


Fig.1 Typical Saturation Voltage Characteristics

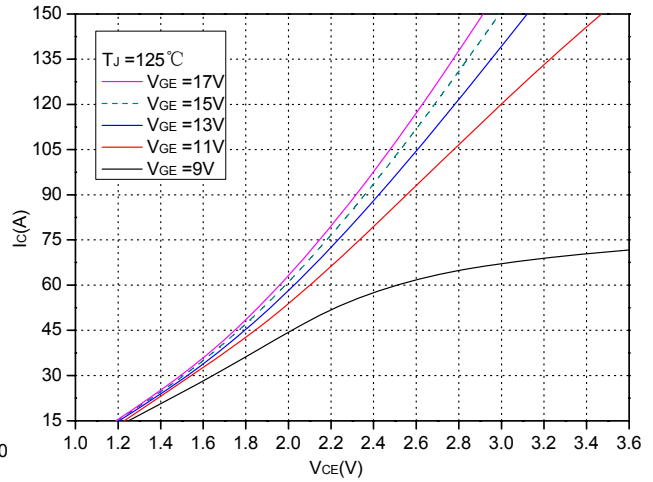


Fig.2 Typical Output Characteristics

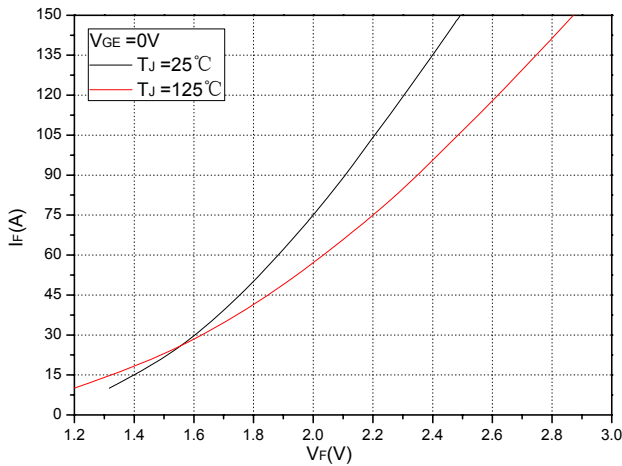


Fig.3 Forward Characteristics of FWD

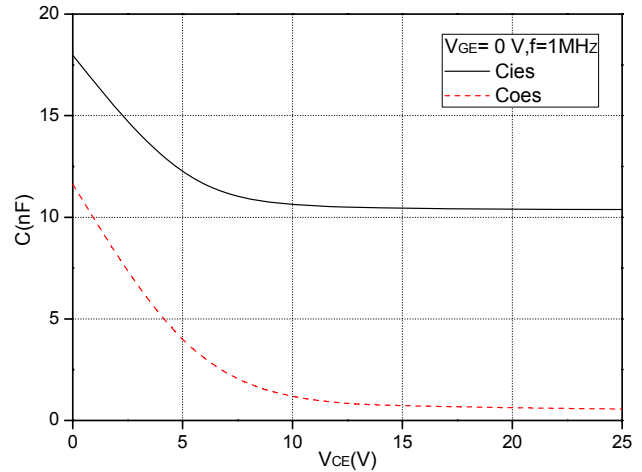


Fig.4 Capacitance Characteristics

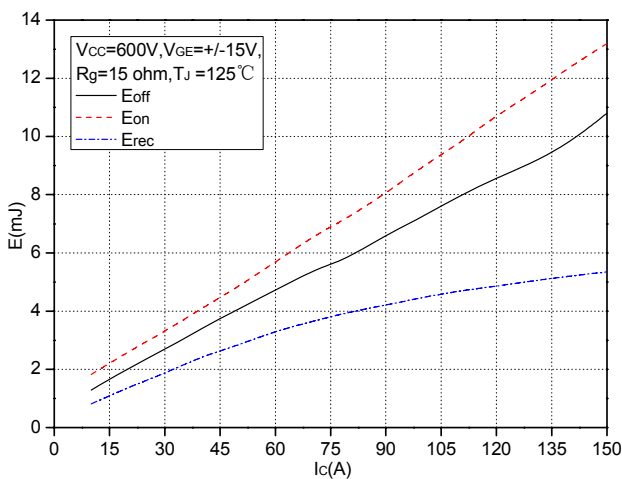


Fig.5 Typical Switching Loss vs. Collector Current

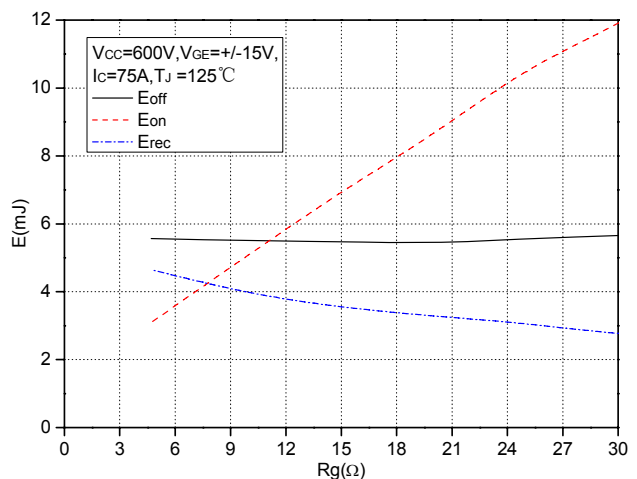


Fig.6 Typical Switching Loss vs. Gate Resistance

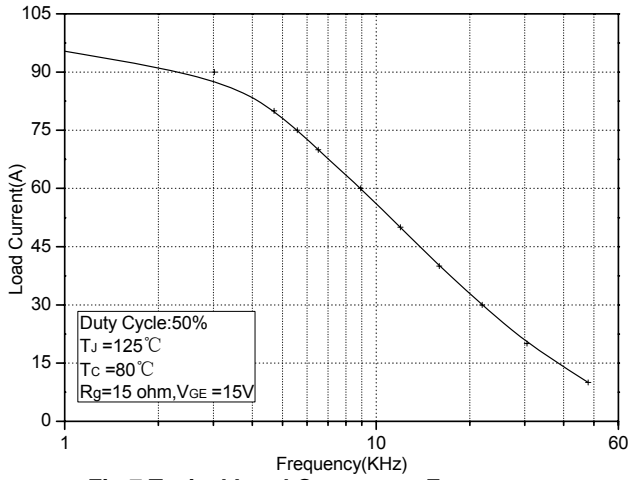


Fig.7 Typical Load Current vs. Frequency

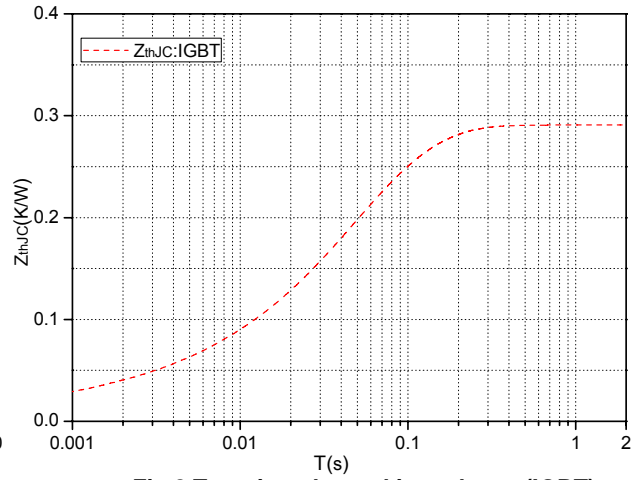


Fig.8 Transient thermal impedance (IGBT)

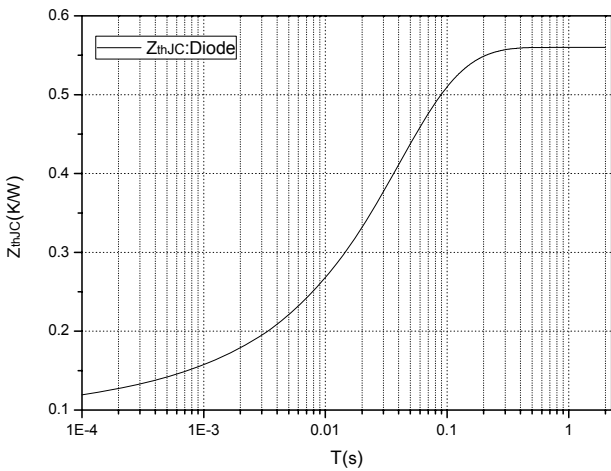


Fig.9 Transient thermal impedance (Diode)

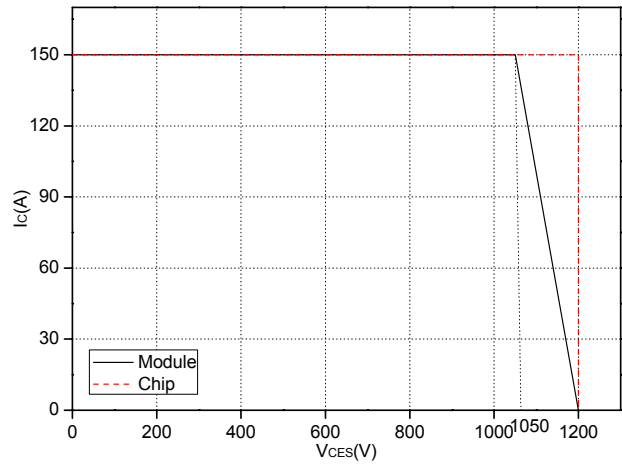
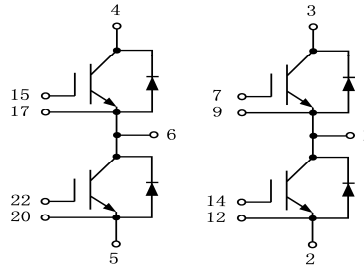
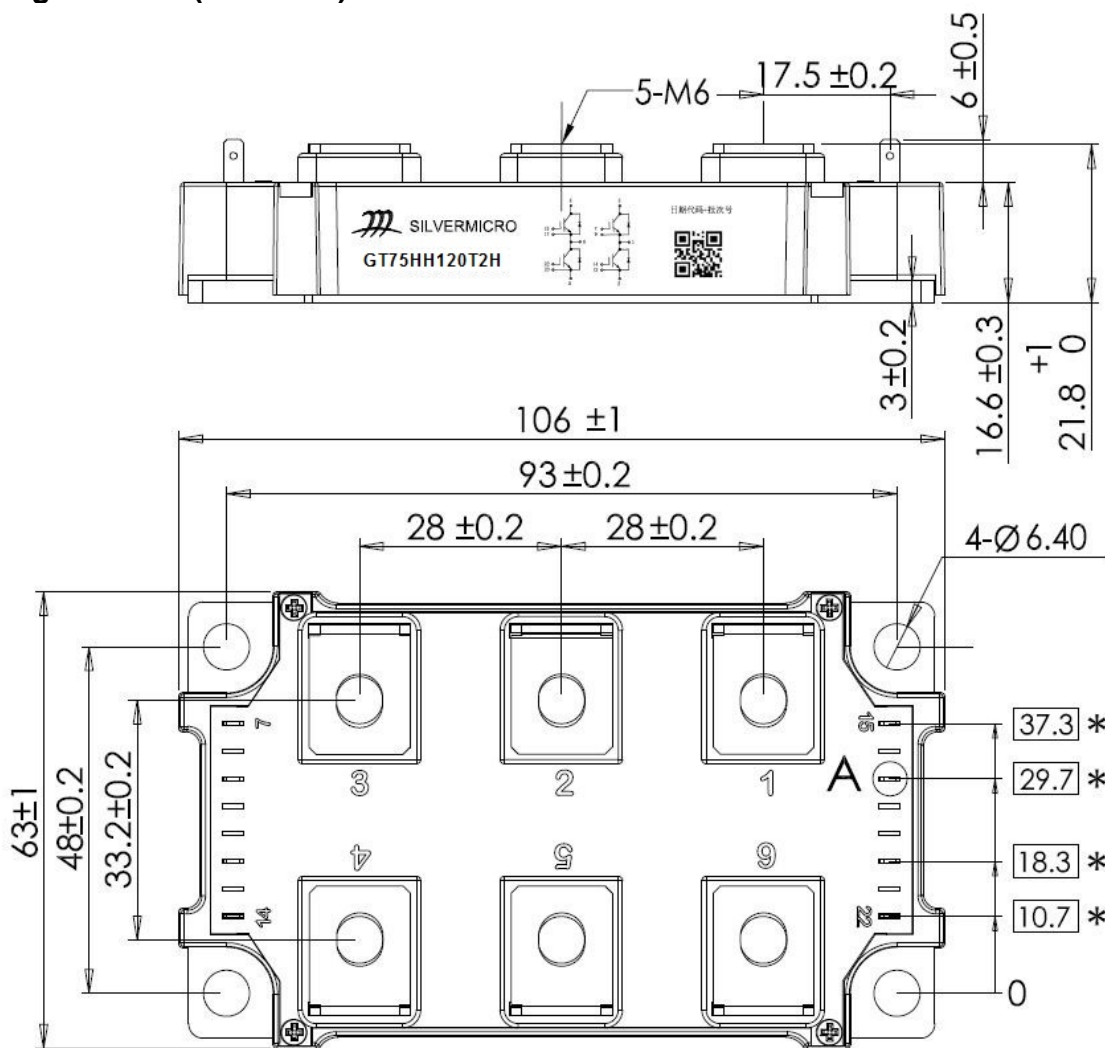


Fig.10 Reverse Bias Safe Operation Area (RBSOA)

Internal Circuit:



Package Outline (Unit: mm):



* =all dimensions with tolerance of $\begin{matrix} \oplus \\ \ominus \end{matrix} \ 0.5$

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